



Please type a plus sign (+) inside this box

PTO/SB/08A (08-00)

Approved for use through 10/31/2002. OMB 0651-0031

U.S. Patent and Trademark Office: U.S. DEPARTMENT OF COMMERCE

Under the Paperwork Reduction Act of 1995, no persons are required to respond to a collection of information unless it contains a valid OMB control number.

<b>Substitute for form 1449A/PTO</b> <b>INFORMATION DISCLOSURE STATEMENT BY APPLICANT</b> (use as many sheets as necessary)		<b>Complete if Known</b>	
		Application Number	10/726,529
		Filing Date	December 4, 2003
		First Named Inventor	Hongyong ZHANG
		Group Art Unit	2823
Examiner Name	K. Nguyen		
Attorney Docket Number	740756-2675		
Sheet	1	of	4

U.S. PATENT DOCUMENTS						
Examiner Initials <sup>*</sup>	Cite No. <sup>1</sup>	U.S. Patent Document		Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YYYY	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number	Kind Code <sup>2</sup> (if known)			
M		5,766,344		Zhang et al	06/16/98	
		4,266,986		Benton et al	05/12/91	
		4,552,595		Hoga	11/12/85	
		4,555,301		Gibson et al	11/25/85	
		4,569,697		Tsu et al	02/11/86	
		4,638,110		Erbert	01/20/87	
		5,306,651		Masumo et al	04/26/94	
		5,352,291		Zhang et al	10/04/94	
		5,372,836		Imahashi et al	12/13/94	
		4,933,298		Hasegawa	06/12/90	
		4,885,260		Ban et al	12/05/89	
		3,771,026		Asai et al	11/06/73	
		5,114,876		Weiner	05/19/92	
		4,758,533		Magee et al.	07/19/88	
		US-5,151,383		Meyerson et al.	09/29/1992	
		US-5,861,337		Zhang et al.	01/19/1999	
		US-5,849,043		Zhang et al.	12/15/1998	
		US-5,424,244		Zhang et al.	06/13/1995	
		US-5,200,630		Nakamura et al.	04/1993	
		US-5,104,455		Yokota et al.	04/1992	

Examiner Signature: <u>Quoc Hoang</u>	Date Considered: <u>5/04</u>
--	---------------------------------

\*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

Sheet 2 of 4Form PTO-1449  
(Rev. 8-83)U.S. Department of Commerce  
Patent and Trademark Office

Attorney Docket:

740756-2675

Serial No.

10/726,529

## INFORMATION DISCLOSURE STATEMENT

(Use several sheets if necessary)

Applicant: Hongyong ZHANG

Filing Date: December 4, 2003 | Group: 2823

## FOREIGN PATENT DOCUMENTS

Examiner Initials <sup>*</sup>	Cite No. <sup>1</sup>	Foreign Patent Document		Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YYYY	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T <sup>6</sup>
		Office <sup>2</sup>	Kind Code <sup>3</sup> Number <sup>4</sup> (if known)				
m		JP	02-224339	Masayoshi et al.	09/06/90		Full
		JP	57-202729	Tadashi et al.	12/11/82		Abstract
		JP	01-259530	Asakawa	10/17/89		Full
		JP	03-148836	Kazuhiro et al.	06/25/91		Abstract
		JP	61-255016	Yamazaki	11/86		Abstract
		JP	58-092216	Haruhiko et al.	06/83		Abstract
		JP	56-142651	Morikuri	11/81		Abstract
		JP	86115		03/90		Abstract
		JP	02-114521	Noguchi et al.	04/26/1990		Abstract
		JP	03-178125	Arima et al.	08/02/1991		Abstract
		JP	60-216538	Shimizu et al.	10/30/1985		Abstract
		JP	60-245174	Yamazaki	12/04/1985		Abstract
		JP	62-264619	Samejima	11/17/1987		Abstract
		JP	61-199640	Samejima et al.	09/04/1986		Abstract

Examiner:

Signature:

Qua Huang

Date

Considered:

5/04

\*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.



Sheet 3 of 4

Form PTO-1449  
(Rev. 8-83)U.S. Department of Commerce  
Patent and Trademark Office

Attorney Docket:

740756-2675

Serial No.

10/726,529

## INFORMATION DISCLOSURE STATEMENT

(Use several sheets if necessary)

Applicant: Hongyong ZHANG

Filing Date: December 4, 2003 Group: 2823

## OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

my	Kawachi et al., "Large-Area Doping Process for Fabrication of poly-Si Thin Film Transistors Using Bucket Ion Source and XeCl Excimer Laser Annealing," Japanese Journal of Applied Physics, Vol. 29, No. 12, December 1990, pp. L2370-2372.
	Inoue et al., "Low Temperature CMOS Self-Aligned Poly-Si TFTs and Circuit Scheme Utilizing New Ion Doping and Masking Technique", 1991 IEEE 20.1.1-20.1.4 IEDM, August 12, 1991, pp. 555-558.
	Stringfellow, "Vapor Phase Growth", Crystal Growth, Vol. 16, 2 <sup>nd</sup> Edition, Pampline, Chapter 5, pp. 181-202.
	Takenaka et al., "High Mobility Poly-Si Thin Film Transistors Using Solid Phase Crystallized A-Si Films Deposited by Plasma-Enhanced Chemical Vapor Deposition", Japanese Journal of Applied Physics, Vol. 29, No. 12, December 1990.
	Boyd, "Laser-Enhanced Oxidation of Si", Applied Physics Letters, Vol. 42, No. 8, pp. 728-30.
	Craciun et al., "Direct Laser Synthesis of Thin Silicon and Germanium Nitride/Oxynitride Layers", Nucl. Instrum. Methods Phys. Res. B, Beam Interact. Mater At., Vol. B65, No. 1-4, pp. 115-18 (March 1992).
	Craciun et al., "Direct Oxynitride Synthesis by Multipulse Excimer Laser Irradiation of Silicon Wafers in a Nitrogen-Containing Ambient Environment", J. Appl. Phys, Vol. 68, No. 5, September 1, 1990, pp. 2509-11.
	Russell et al., "Bipolar Transistors in Silicon-on-Sapphire (SOS) Effects of Nanosecond Thermal Processing", IEEE SOS/SOI Tech. Conf. Proceedings October 24, 1990.
	Wolf et al., Silicon Processing for the VLSI Era Volume 1: Process Technology, Lattice Press, Sunset Beach, CA, (1989), pp. 471, 476-479.
	Carey et al., "Submicrometer CMOS Device Fabrication Using Gas Immersion Laser Doping (GILD)", IEEE Transactions on Electron Devices, Vol. 35, No. 12, December 1988, p. 2429.
	Weiner et al., "Thin-Base Bipolar Transistor Fabrication Using Gas Immersion Laser Doping", IEEE Electron Dev. Lett., Vol. 10, No. 6, (1989), pp. 260-263.
	Turner et al., "Gas Immersion Laser Diffusion for Efficient Cell Fabrication and Grain Boundary Research", 16 <sup>th</sup> IEEE Photovoltaic Specialist Conference, San Diego, CA, September 27-30, 1982, pp. 775-780.
	Carey et al., "Ultra-Shallow High Concentration Boron Profiles for CMOS Processing", IEEE Electron Dev. Lett., Vol. EDL-6, No. 6, (1985), pp. 291-293
✓	Carey et al., "Fabrication of Submicrometer MOSFETS Using Gas Immersion Laser Doping (GILD)," IEEE Electron Dev. Lett., Vol. EDL-7, No. 7, (1986), pp. 440-442.
my	Weiner et al., "Measurement of Melt Depth Limited Diffusion in Gas Immersion Laser Doped Silicon Using an Improved Laser System," (In Proceedings of the Symposium on Laser Processing for Microelectronic Applications) (1988), pp. 53-61.

Examiner  
Signature:

Quri Hsiao

Date

Considered:

5/04

\*EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

